Preliminary

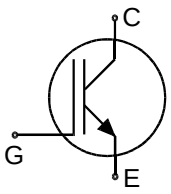
SIGC121T120R2C

IGBT Chip in NPT-technology

FEATURES:
- 1200V NPT technology 200µm chip
- low turn-off losses
- short tail current
- positive temperature coefficient
- easy paralleling
- integrated gate resistor

This chip is used for:
- power module
  BSM 75GD120DN2

Applications:
- drives



Chip Type	V_{CE}	I_{Cn}	Die Size	Package	Ordering Code
SIGC121T120R2C	1200V	75A	11.08 X 11.08 mm^2	sawn on foil	Q67041-A4682-A003

MECHANICAL PARAMETER:

Raster size	11.08 X 11.08	mm^2
Emitter pad size	8 x (2.99 x 1.97)	
Gate pad size	1.46 x 0.8	
Area total / active	122.8 / 99.6	
Thickness	200	µm
Wafer size	150	mm
Flat position	90	grd
Max.possible chips per wafer	106 pcs	
Passivation frontside	Photoimide	
Emitter metallization	3200 nm Al Si 1%	
Collector metallization	1400 nm Ni Ag –system suitable for epoxy and soft solder die bonding	
Die bond	electrically conductive glue or solder	
Wire bond	Al, <500µm	
Reject Ink Dot Size	∅ 0.65mm ; max 1.2mm	
Recommended Storage Environment	store in original container, in dry nitrogen, < 6 month	

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MAXIMUM RATINGS:

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CE}	1200	V
DC collector current, limited by T_{jmax}	I_C	103	A
Pulsed collector current, t_p limited by T_{jmax}	I_{cpuls}	206	A
Gate emitter voltage	V_{GE}	±20	V
Operating junction and storage temperature	T_j, T_{stg}	-55 ... +150	°C

STATIC CHARACTERISTICS (tested on chip), T_j=25 °C, unless otherwise specified:

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Collector-emitter breakdown voltage	$V_{(BR)CES}$	V_{GE}=0V , I_C=4mA	1200			V
Collector-emitter saturation voltage	$V_{CE(sat)}$	V_{GE}=15V, I_C=75A	2.0	2.5	3.0	
Gate-emitter threshold voltage	$V_{GE(th)}$	I_C=3mA , V_{GE}=V_{CE}	4.5	5.5	6.5	
Zero gate voltage collector current	I_{CES}	V_{CE}=1200V , V_{GE}=0V			500	µA
Gate-emitter leakage current	I_{GES}	V_{CE}=0V , V_{GE}=30V			480	nA
Integrated gate resistor	R_{Gint}			5		Ω

ELECTRICAL CHARACTERISTICS (tested at component):

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Input capacitance	C_{iss}	V_{CE}=25V,	-	5.1	-	nF
Output capacitance	C_{oss}	V_{GE}=0V,	-	0.72	-	
Reverse transfer capacitance	C_{rss}	f=1MHz	-	0.38	-	

SWITCHING CHARACTERISTICS (tested at component), Inductive Load

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Turn-on delay time	$t_{d(on)}$	T_j=125°C	-	30	60	ns
Rise time	t_r	V_{CC}=600V,	-	70	140	
Turn-off delay time	$t_{d(off)}$	I_C=75A,	-	450	600	
Fall time	t_f	V_{GE}=+15/-15V, R_G=15 Ω	-	70	100	

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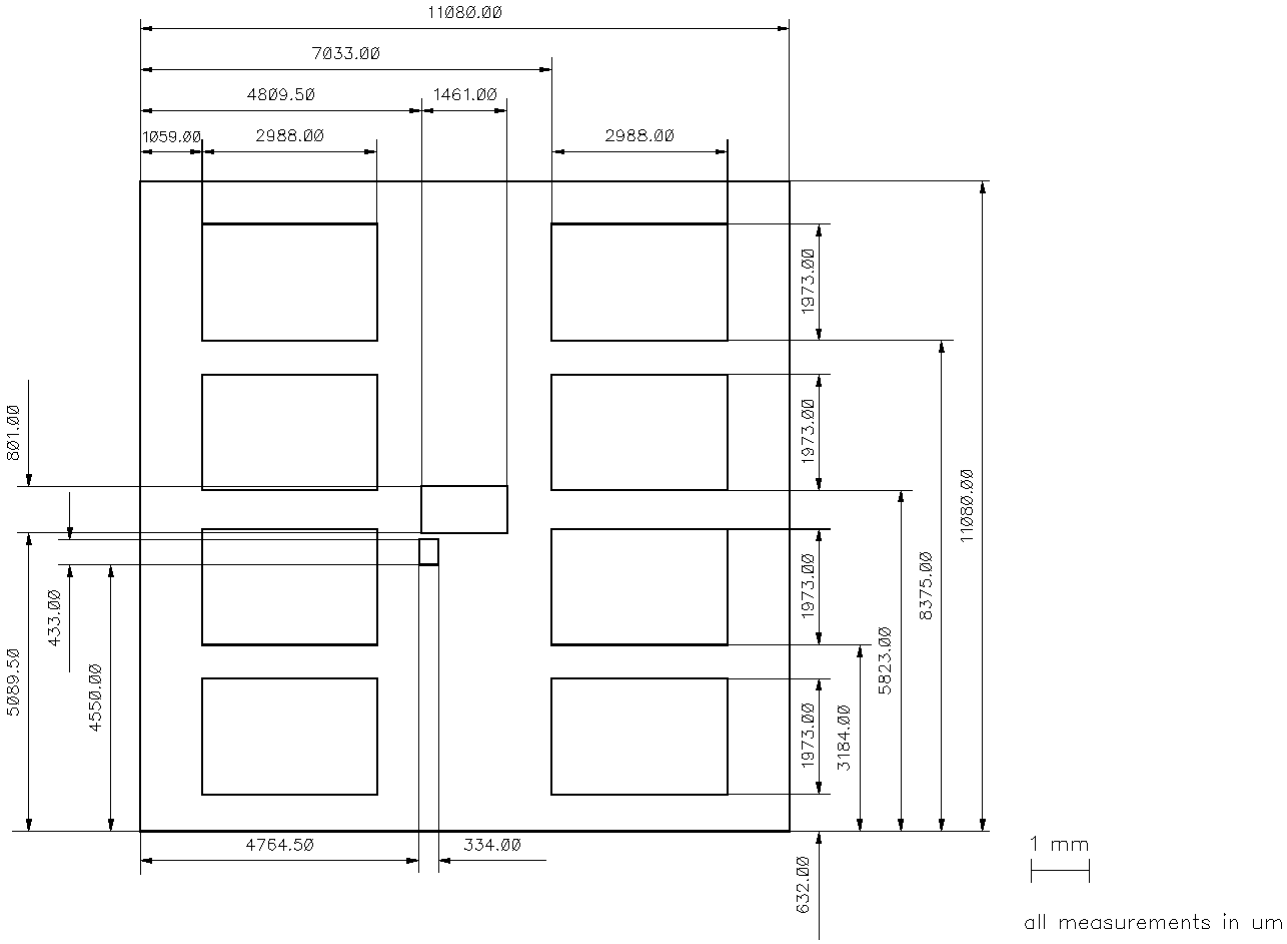
CHIP DRAWING:



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FURTHER ELECTRICAL CHARACTERISTICS:

This chip data sheet refers to the device data sheet	BSM 75GD120DN2	ECONOPACK3

DESCRIPTION:

AQL 0,65 for visual inspection according to failure catalog
Electrostatic Discharge Sensitive Device according to MIL-STD 883
Test-Normen Villach/Prüffeld

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